

DCF010

Silicon Epitaxial Planar Type (Anode Common)

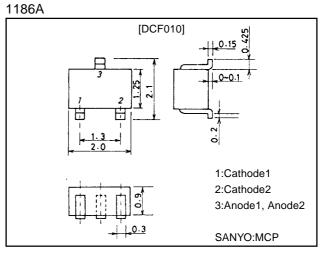
Ultrahigh-Speed Switching Diode

Features

- · Ideally suited for use in hybrid ICs because of very small-sized package.
- · Fast switching speed.
- · Small interterminal capacitance.

Package Dimensions

unit:mm



Specifications

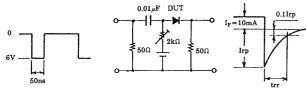
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V _{RM}		85	V
Reverse Voltage	V _R		80	V
Peak Forward Current	I _{FM}	Unit rating	300	mA
		Total rating	450	mA
Average Rectified Current	IO	Unit rationg	100	mA
		Total tating	150	mA
Surge Current (1µs)	IFSM	Unit rating	4	А
		total rating	6	А
Allowable Power Dissipation	Р		100	mW
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C

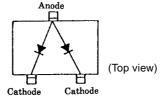
Electrical Characteristics at Ta = 25°C

Symbol	Conditions	Ratings			Unit
		min	typ	max	
V _{F1}	I _F =1mA		0.61		V
V _{F2}	I _F =10mA		0.74		V
V _{F3}	I _F =100mA			1.20	V
I _{R1}	V _R =30V			0.1	μA
I _{R2}	V _R =80V			0.5	μA
С	V _R =0V, f=1MHz			4.0	pF
trr	I _F =10mA, V _R =6V, R _L =50Ω, Irr=0.1Irp			4.0	ns
	VF1 VF2 VF3 IR1 IR2 C	VF1 IF=1mA VF2 IF=10mA VF3 IF=100mA IR1 VR=30V IR2 VR=80V C VR=0V, f=1MHz	VF1 IF=1mA min VF2 IF=10mA VF3 IF=100mA IR1 VR=30V IR2 VR=80V C VR=0V, f=1MHz	Symbol Conditions min typ VF1 IF=1mA 0.61 0.61 VF2 IF=10mA 0.74 0.74 VF3 IF=100mA 0 0.74 IR1 VR=30V 0 0 IR2 VR=80V 0 0 C VR=0V, f=1MHz 0 0	Symbol Conditions min typ max VF1 IF=1mA 0.61 0.61 VF2 IF=10mA 0.74 0.74 VF3 IF=100mA 0.1 1.20 IR1 VR=30V 0.1 0.1 IR2 VR=80V 0.5 0.5 C VR=0V, f=1MHz 4.0

Reverse Recovery Time Test Circuit

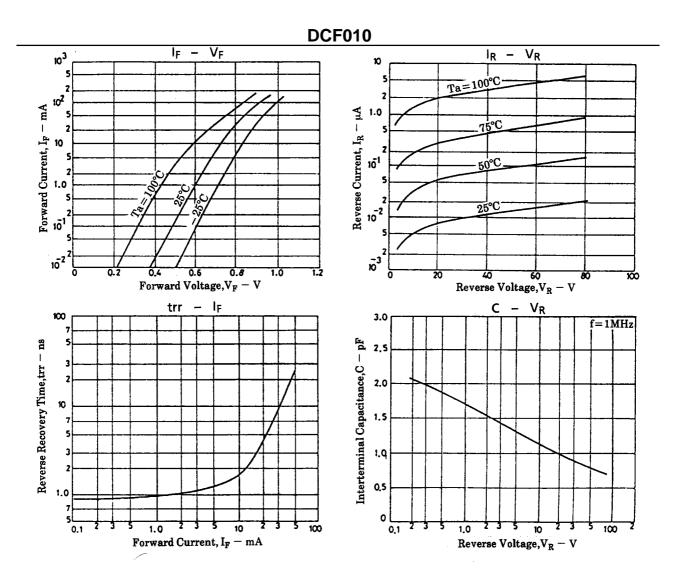


Electrical Connection



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